

N-channel TrenchMOS logic level FET Rev. 04 — 7 April 2010

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

### **1.3 Applications**

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters

### 1.4 Quick reference data

#### Suitable for logic level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- General purpose power switching
- Solenoid drivers

Table 1.	Quick reference da	ita				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	14.8	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	-	59	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source	$V_{GS}$ = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	86	99	mΩ
	on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	91	104	mΩ
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 14.8 \text{ A};  V_{\text{sup}} \leq 100 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  V_{\text{GS}} = 5 \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	35	mJ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 5 \text{ A};$ $V_{DS} = 80 \text{ V}; \text{ see } \overline{\text{Figure } 13}$	-	4.7	-	nC
						-

# nexperia

### N-channel TrenchMOS logic level FET

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

Table 3.	Ordering information			
Type num	ber	Package		
		Name	Description	Version
BUK9Y104	-100B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
-					٩٢.	-	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	100	V
V <sub>GS</sub>	gate-source voltage			-15	-	15	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$		-	-	14.8	A
		$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>		-	-	10.48	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>		-	-	59	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	-	59	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	-	14.8	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \text{ ms}; \text{ pulsed}; T_{mb} = 25 \text{ °C}$		-	-	59	А
Avalanche ru	ggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 14.8 \; A; \; V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 5 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$		-	-	35	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy	see Figure 2	[1][2][3] [4]	-	-	-	J

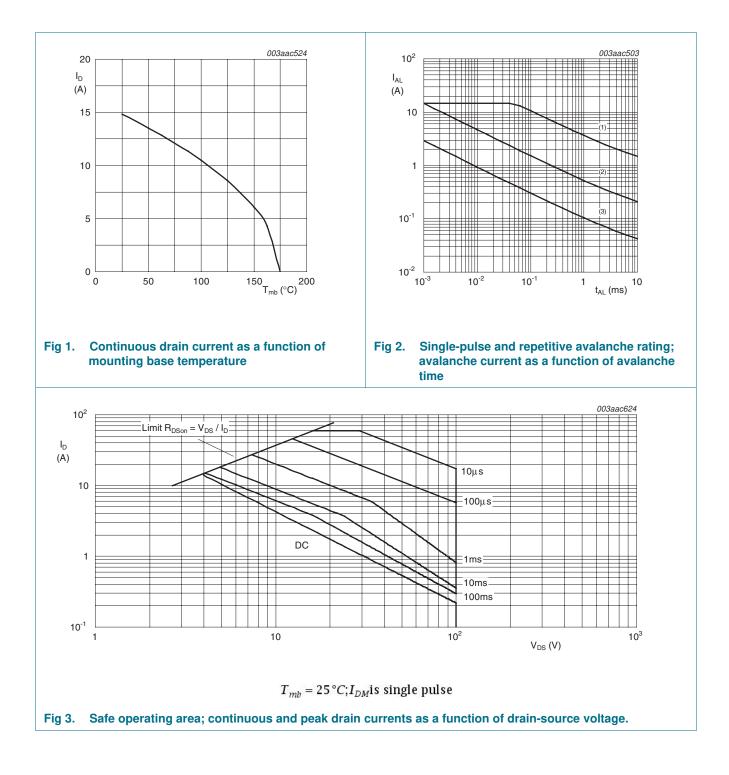
[1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.

### BUK9Y104-100B



### 5. Thermal characteristics

mbol	Parameter	Conditions	Min Typ Max Uni
(j-mb)	thermal resistance from junction to mounting base	see <u>Figure 4</u>	2.53 K/W
10			003aac483
Z <sub>th (j-mb)</sub> (K/W)			
1	δ = 0.5		
	0.1		
10 <sup>-1</sup>	0.05		$P \qquad \delta = \frac{t_p}{T}$
	single shot		$\begin{array}{c c} \hline \\ \hline $
10 <sup>-2</sup> 1(	0 <sup>-6</sup> 10 <sup>-5</sup>	10 <sup>-4</sup> 10 <sup>-3</sup>	$10^{-2}$ $10^{-1}$ $t_{p}$ (s)

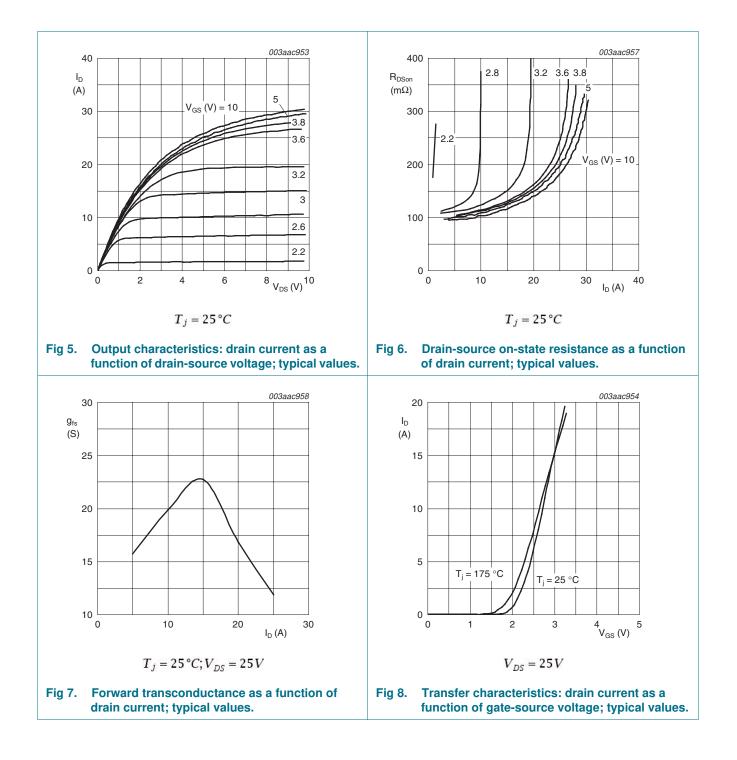
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### 6. Characteristics

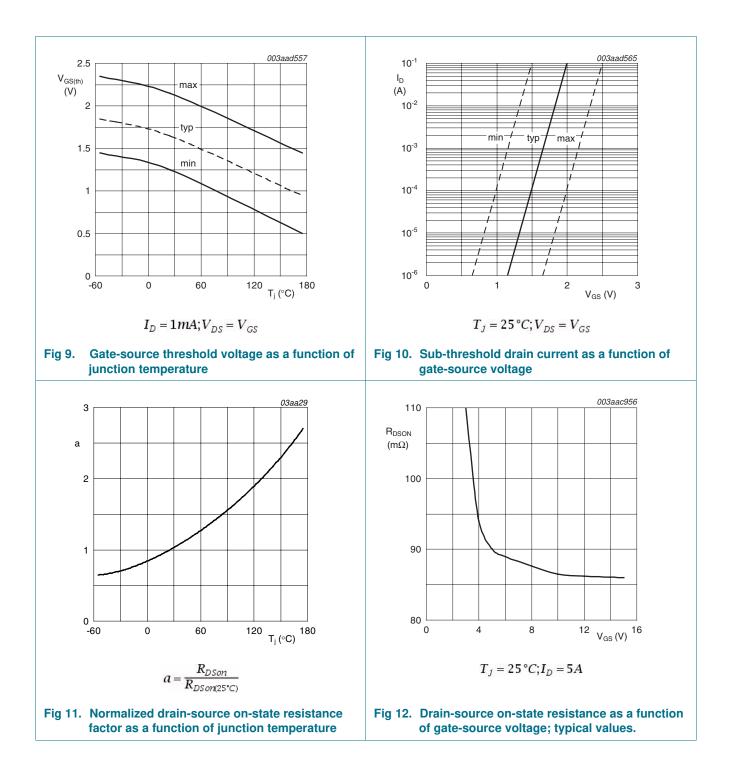
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	100	-	-	V
	breakdown voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 9; see Figure 10	1.25	1.65	2.15	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 V; V_{GS} = 15 V; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -15 V; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 5 \text{ A}; \text{ T}_{j} = 25 ^{\circ}\text{C}$	-	86	99	mΩ
T	resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	-	-	270	mΩ
		$V_{GS}$ = 4.5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C	-	-	107	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	91	104	mΩ
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	11	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 13	-	1.7	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.7	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	854	1139	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 14$	-	87	105	pF
C <sub>rss</sub>	reverse transfer capacitance		-	42	58	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 6 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	15	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega$	-	8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	36	-	ns
t <sub>f</sub>	fall time		-	6	-	ns
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
rr	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	79	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 V$	-	190	-	nC

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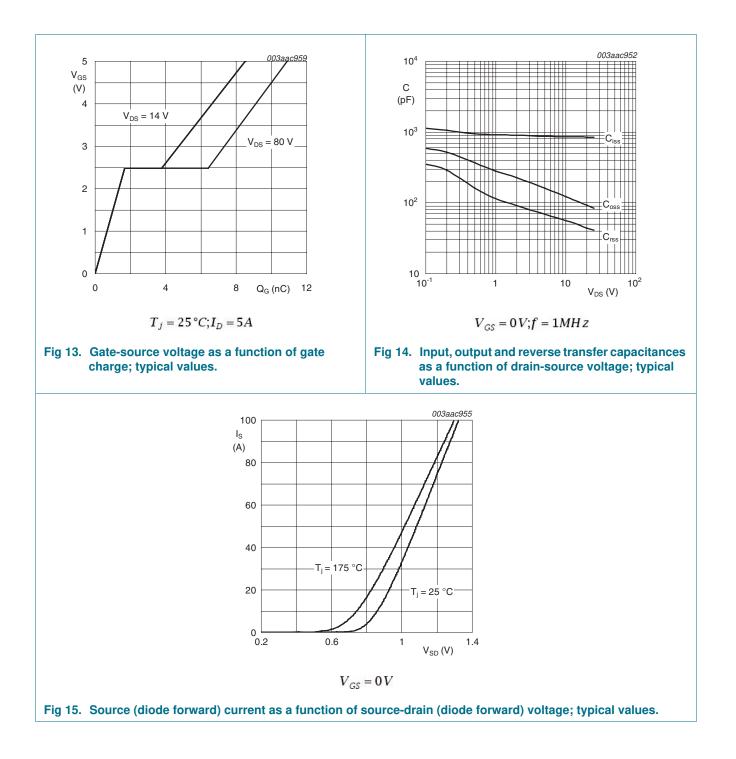
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### BUK9Y104-100B

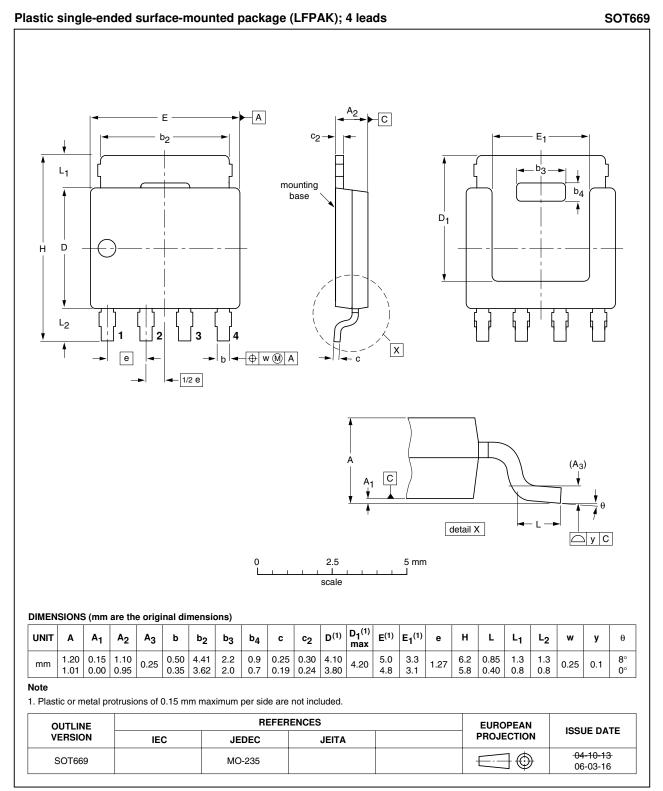


### BUK9Y104-100B



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### 7. Package outline



#### Fig 16. Package outline SOT669 (LFPAK)

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### 8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9Y104-100B_4	20100407	Product data sheet	-	BUK9Y104-100B_3
Modifications:	<ul> <li>Status char</li> </ul>	nged from objective to proc	duct.	
BUK9Y104-100B_3	20100211	Objective data sheet	-	BUK9Y104-100B_2

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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